

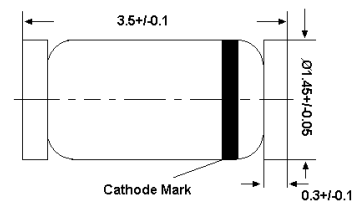
LL4150

Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High reliability
- High conductance
- For general purpose switching applications

LL-34



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Average Rectified Forward Current	$I_{F(AV)}$	200	mA
Forward Continuous Current	I_{FM}	300	mA
Power Dissipation	P_{tot}	500	mW
Junction temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +175	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 50\text{ V}$	I_R	100	nA
Reverse Recovery Time at $I_F = I_R = 10\text{ to }200\text{ mA}$, to $0.1\text{ }I_F$	t_{rr}	4	ns